

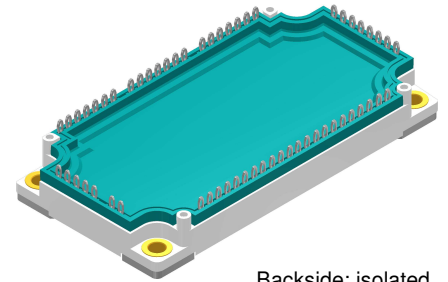
High Voltage Standard Rectifier Module

3~ Rectifier
$V_{RRM} = 2200\text{ V}$
$I_{DAV} = 660\text{ A}$
$I_{FSM} = 5000\text{ A}$

3~ Rectifier Bridge + NTC

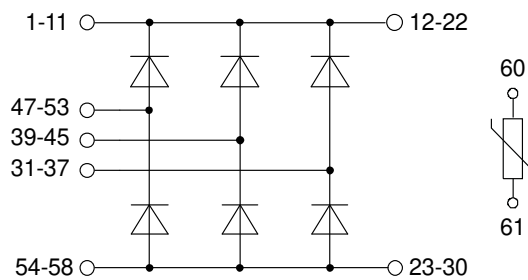
Part number

MDNA660U2200PTEH



Backside: isolated

E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: E3-Pack

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- PressFit-Pins for PCB mounting
- Height: 17 mm
- Base plate: Copper internally DCB isolated
- Advanced power cycling
- Phase Change Material available

Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

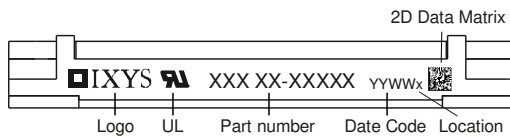
- to perform joint risk and quality assessments;

- the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage			$T_{VJ} = 25^{\circ}C$		2300	V
V_{RRM}	max. repetitive reverse blocking voltage			$T_{VJ} = 25^{\circ}C$		2200	V
I_R	reverse current	$V_R = 2200$ V		$T_{VJ} = 25^{\circ}C$		400	μA
		$V_R = 2200$ V		$T_{VJ} = 150^{\circ}C$		6	mA
V_F	forward voltage drop	$I_F = 220$ A		$T_{VJ} = 25^{\circ}C$		1.28	V
		$I_F = 660$ A				1.95	V
		$I_F = 220$ A		$T_{VJ} = 125^{\circ}C$		1.19	V
		$I_F = 660$ A				1.95	V
I_{DAV}	bridge output current	$T_C = 85^{\circ}C$		$T_{VJ} = 150^{\circ}C$		660	A
		rectangular	$d = \frac{1}{3}$				
V_{FO}	threshold voltage			$T_{VJ} = 150^{\circ}C$		0.77	V
r_F	slope resistance					1.8	m Ω
						} for power loss calculation only	
R_{thJC}	thermal resistance junction to case					0.15	K/W
R_{thCH}	thermal resistance case to heatsink				0.075		K/W
P_{tot}	total power dissipation			$T_C = 25^{\circ}C$		830	W
I_{FSM}	max. forward surge current	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^{\circ}C$		5.00	kA
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		5.40	kA
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^{\circ}C$		4.25	kA
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		4.59	kA
I^2t	value for fusing	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^{\circ}C$		125.0	kA ² s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		121.3	kA ² s
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^{\circ}C$		90.3	kA ² s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		87.6	kA ² s
C_J	junction capacitance	$V_R = 700$ V; $f = 1$ MHz		$T_{VJ} = 25^{\circ}C$		158	pF

Package E3-Pack		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			30	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				270		g
M_D	mounting torque		3		6	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	12.0			mm
V_{ISOL}	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V

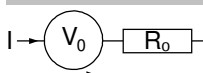

Part description

- M = Module
- D = Diode
- N = High Voltage Standard Rectifier
- A = (>= 2000V)
- 660 = Current Rating [A]
- U = 3- Rectifier Bridge
- 2200 = Reverse Voltage [V]
- PT = PressFit-Pin, Thermistor
- EH = E3-Pack
- = Hyphen
- PC = Phase Change Material

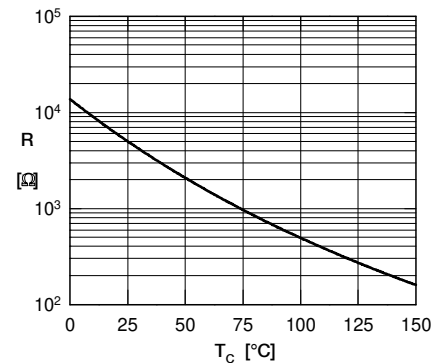
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MDNA660U2200PTEH	MDNA660U2200PTEH	Blister	24	516663
Alternative	MDNA660U2200PTEH-PC	MDNA660U2200PTEH	Blister	24	514482

Temperature Sensor NTC

Symbol	Definition	Conditions	min.	typ.	max.	Unit
R_{25}	resistance	$T_{VJ} = 25^\circ$	4.85	5	5.15	kΩ
$B_{25/50}$	temperature coefficient			3375		K

Equivalent Circuits for Simulation
** on die level*
 $T_{VJ} = 150^\circ\text{C}$

Rectifier

$V_{0\ max}$	threshold voltage	0.77				V
$R_{0\ max}$	slope resistance *	0.57				mΩ



Typ. NTC resistance vs. temperature

Rectifier

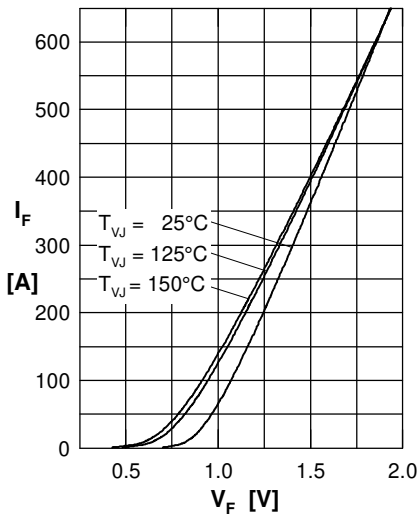


Fig. 1 Forward current versus voltage drop per diode

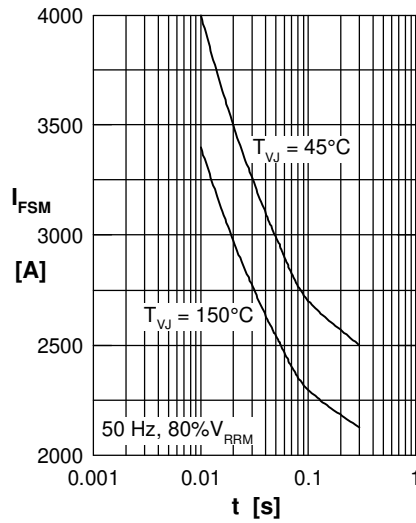


Fig. 2 Surge overload current vs. time per diode

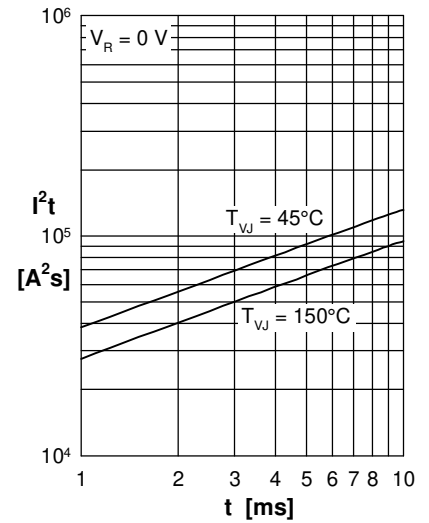


Fig. 3 I^2t versus time per diode

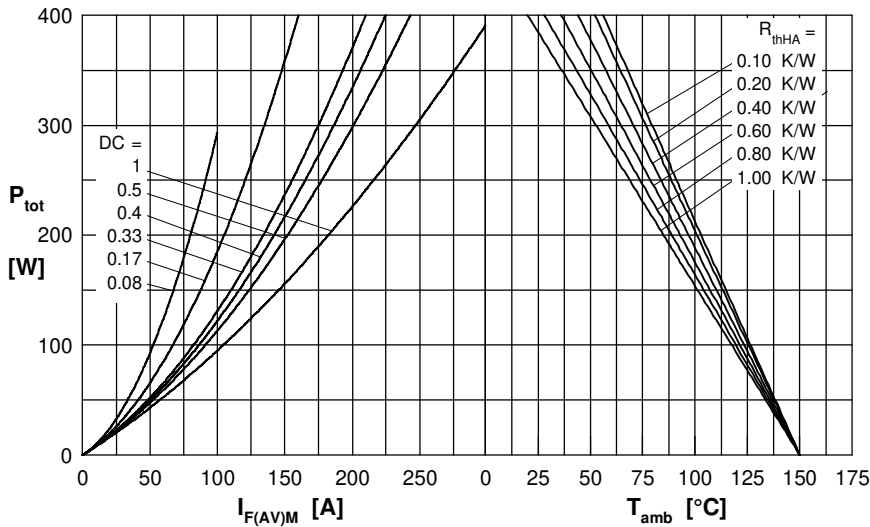


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

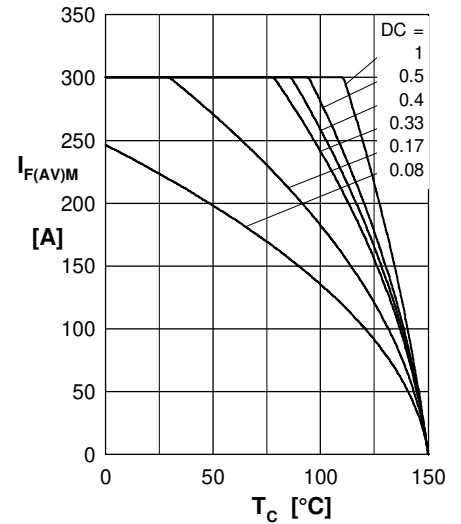


Fig. 5 Max. forward current vs. case temperature per diode

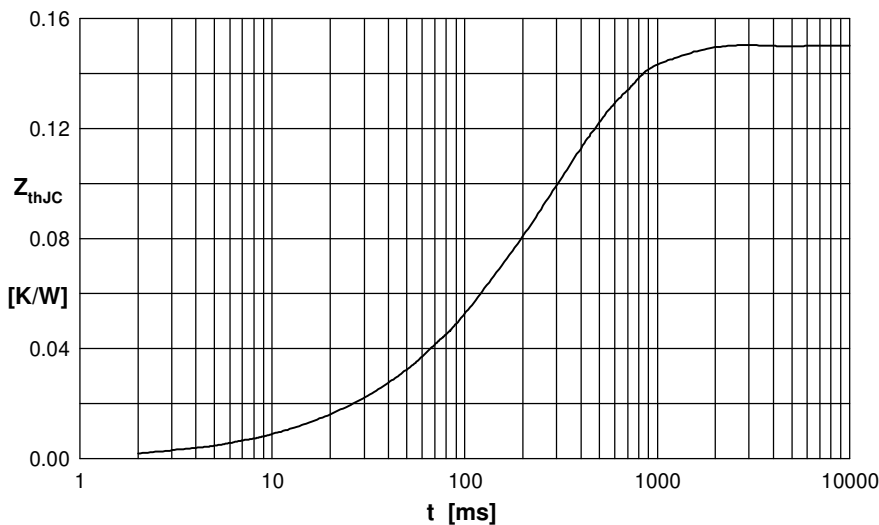


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thjC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.006	0.015
2	0.017	0.080
3	0.039	0.220
4	0.088	0.380